

Fabrication and Magnetic property of Co/Pt/*r*-Cr₂O₃ Multilayer

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Abstract: We report the crystal structures and magnetic properties of *r*-plane oriented [Pt/Co]₃/Pt/Cr₂O₃ multilayers fabricated by DC-RF magnetron sputtering method. From the 2θ - θ profile, the film peaks appeared at a lower angle than that of the substrate peaks in 2θ . The lattice spacing of *r*-plane was 0.363 nm. This value is in agreement with that of the bulk, indicating that the film was grown without stress from the substrate. From the reciprocal space mapping, both the substrate and film peaks were visible for (2 -2 0 10) plane, while no peaks were observed for the (2 -2 0 8) plane. The magnetic property of the multilayer was investigated from magnetic field (H) dependences of the in-plane and out-of-plane magnetizations (M). The magnetic moments of in-plane and out-of-plane were 0.30 μ_B and 1.53 μ_B respectively per a cobalt ion at 5 K. These values are smaller than that of bulk, suggesting that the Co film may be thinner than we expected or may have island structure.

1. Introduction

In order to realize the magnetization switching by an application of an electric field, we fabricate the multilayer of ferromagnetic (FM) metal and antiferromagnetic (AFM) showing magnetoelectric (ME) effect. FM metal and Cr₂O₃ multilayers have drawn much attention recently because the magnetic moment in FM metal can be reversed with the applied electrical field^{[1][2]}. The origin of the reversal is the exchange bias field (H_{EB}) applied to the FM metal because of the magnetic coupling between spins in FM metal and Cr spins at the interface.

As the magnitude of H_{EB} is proportional to the magnitude of spins at the top most surface of AFM (S_{AF}), large S_{AF} is required for large H_{EB} ^[3]. However, the net magnetic moment is zero on the top surface of the pseudo-perovskite structure of AFM materials. On the other hand, all Cr spins on the *r*-surface of Cr₂O₃ single crystal definitely show the two-dimensional (2D) FM ordering even though the surface shows step-terrace structure as shown in Fig. 1. Such the FM structure at the surface has the potential to obtain a large value of the H_{EB} ^[4]. Therefore we fabricate FM metal and *r*-oriented Cr₂O₃ multilayers.

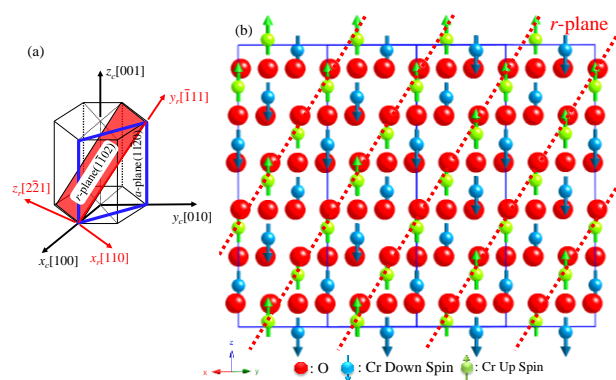


Fig.1. Crystal structure of Cr₂O₃.

(a) Sketches of crystal planes. *r*- and *a*-planes are shown as a red and blue planes respectively. (b) View from [1 1 -2 0] direction (vertical to the *a*-plane). *r*-plane is indicated by red dashed line. Large and small circles indicate the O and Cr ions. The arrows indicate the direction of Cr spins. *r*-oriented Cr₂O₃ surface shows 2D FM order of Cr spins.

2. Experimental

The [Pt/Co]₃/Pt/*r*-Cr₂O₃ multilayers were grown on Al₂O₃ (1 -1 0 2) substrate. The substrate was ultrasonically cleaned in acetone and ethanol. The cleaned Al₂O₃(1 -1 0 2) substrate were annealed at 1050°C for 12h in air^[5]. The Cr₂O₃ thin films were grown by the off-axis DC-RF magnetron sputtering method using a 2-inch Cr metal target with an RF power of 80W and a DC current of 0.04A. The substrate temperature was 580 °C. O₂ and Ar gases were flown with the rate of 8 and 2 ccm respectively at 0.20 Pa during the sputtering. The deposition time was 240 min, estimating the film thickness at 200 nm. After the deposition, the film was cooled down to the room temperature in O₂ at 0.1 MPa. FM metal and Pt were deposited by on-axis RF magnetron sputtering method using 2-inch Co and Pt metal target with an RF power of 80W. The deposition times were 29 sec and 47sec for Pt and Co, estimating the average thickness at 0.5 and 1.0 nm, respectively. The surface morphology of the films was evaluated by scanning probe microscopy (SPM; SII Nanotechnology NanoNavi Station, dynamic force mode). The crystal structure of the Cr₂O₃ thin films was evaluated by X-ray diffraction (XRD; Bruker D8 Discover) analysis, and 2θ - θ scan was used to analyze the out-of-plane structure. Detailed analyses were carried out by reciprocal space mapping (RSM). The magnetic measurements were performed with a superconducting quantum interference device (SQUID; QUANTUM DESING, VSM Mode).

3. Results and Discussion

Fig. 2 shows the 2θ - θ XRD spectrum of the *r*-oriented Cr₂O₃ film grown on Al₂O₃ substrate. The film peaks appeared at a lower angle than that of the substrate peaks in 2θ . Pt and Co film peaks appeared between (1 -1 0 2) and (2 -2 0 4) of Cr₂O₃ peaks. The lattice spacing of *r*-plane was 0.363 nm. This values is in agreement with lattice spacing of 0.364 nm for the bulk, indicating that the film was grown without stress from the substrate.

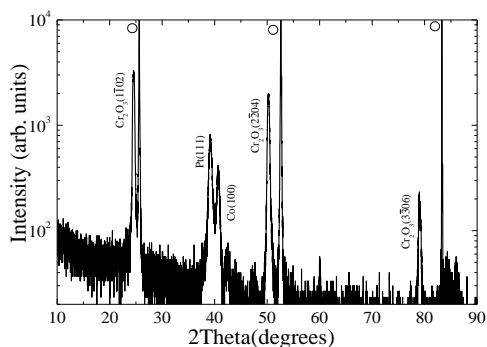


Fig.2. $2\theta - \theta$ XRD patterns.

The film peaks appeared at a lower angle than that of the substrate peaks for 2θ . Pt and Co film peaks appeared between (1 -1 0 2) and (2 -2 0 4) of Cr_2O_3 peaks.

In order to investigate the presence of the twin grains, RSMs were obtained. Fig.3. show the RSMs around the $C_1(2 -2 0 10)$ and $C'_1(2 -2 0 8)$ planes. Both the substrate and film peaks were visible for $C_1(2 -2 0 10)$ plane while no peaks were observed for the $C'_1(2 -2 0 8)$ plane. Fig.4. show the schematic hexagonal structures. $D_1(2 0 -2 8)$ and $C_1(2 -2 0 10)$ peaks coexist in the single grain because of the crystal structure, while $C'_1(2 -2 0 8)$ and $C_1(2 -2 0 10)$ peaks coexist only in the twin grains as the $C'_1(2 -2 0 8)$ plane corresponds to the 60° rotated plane of $D_1(2 0 -2 8)$ plane on the c -axis. Therefore the RSMs in Fig. 3 indicates the Cr_2O_3 film consists of single grain.

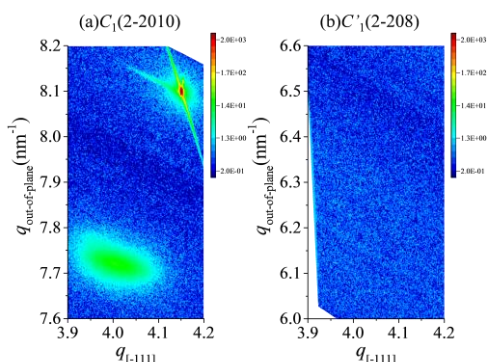


Fig.3. RSM around $\text{Al}_2\text{O}_3(2 -2 0 10)$, $\text{Al}_2\text{O}_3(2 -2 0 8)$.

Both the substrate and film peaks were visible for $C_1(2 -2 0 10)$ while no peaks were observed for the $C'_1(2 -2 0 8)$ planes.

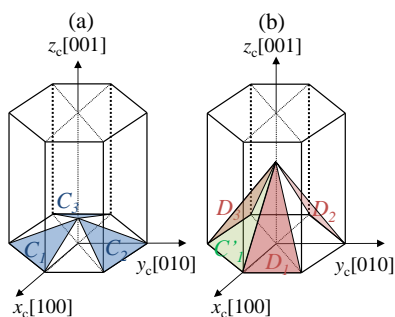


Fig.4. Schematic hexagonal structure

(a) $C_1(2 -2 0 10)$ groups of planes satisfy Bragg's law. C set of $C_1(2 -2 0 10)$, $C_2(0 2 -2 10)$ and $C_3(-2 0 2 10)$. (b) D set of $D_1(2 0 -2 8)$, $D_2(-2 2 0 8)$ and $D_3(0 -2 2 8)$. $C'_1(2 -2 0 8)$ plane corresponds to the 60° rotated plane of $D_1(2 0 -2 8)$ plane on the c -axis.

Fig.5. shows the in-plane and out-of-plane magnetization as a function of the magnetic field at 5 K. Hysteresis loops were observed below 200 K. The magnetic moments of in-plane and out-of-plane were $0.30\mu_B$ and $1.53\mu_B$ respectively per a cobalt ion at 5K. These values are smaller than that of bulk, suggesting that the Co film may be thinner than we expected or may have island structure. Optimization is required on the deposition conditions for the Pt and Co layers.

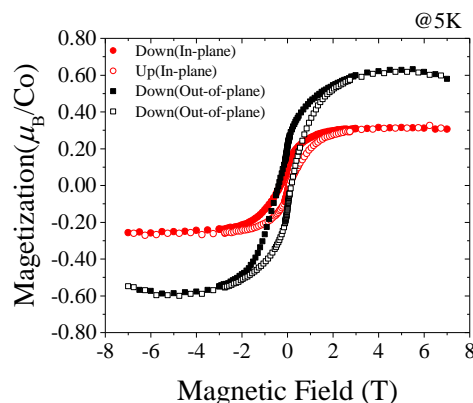


Fig.5. in-plane and out-of-plane magnetization as a function of the magnetic field at 5K.

The magnetic moments of in-plane and out-of-plane were $0.30\mu_B$ and $1.53\mu_B$ respectively per a cobalt ion. These values are smaller than that of bulk.

4. Summary

The $[\text{Pt}/\text{Co}]_3/\text{Pt}/r\text{-Cr}_2\text{O}_3$ multilayers were grown on $\text{Al}_2\text{O}_3(1 -1 0 2)$ substrate using DC-RF magnetron sputtering method. The $2\theta - \theta$ profile and RSMs indicate r -oriented Cr_2O_3 films were grown in single grain. From the in-plane and out-of-plane magnetic property, the magnetic moments of in-plane and out-of-plane were $0.30\mu_B$ and $1.53\mu_B$ respectively per a cobalt ion at 5K. These values are smaller than that of bulk, suggesting that the Co film may be thinner than we expected or may have island structure. Detailed magnetic property will be discussed on improved films.

5. Reference

[1] P. Borisov, A. Hochstrat, X. Chen, W. Kleeman, and Ch. Binek, Phys.Rev. Lett. **94**, 117203 (2005).
 [2] M. Fiebig: J.Phys. D: Appl. Phys. **38** (2005) R123.
 [3] X.Chen, A.Hochstrat, P.Borisov, and W.Kleemann Appl. Phys. Lett. **89** (2006) 202508.
 [4] N. Iwata T. Kuroda and Hiroshi Yamamoto, Jpn. J. Appl. Phys. **51** (2012) 11PG12.
 [5] M.Yoshimoto, T.Maeda, T.Ohnishi, H.Koinuma, O.Ishiyama, M.Shinohara, M.Kubo, R. Miura, and A.Miyamoto: Appl. Phys. Lett. **67**(1995) 2615.